

# Kinetics of interfacial reactions in molten U/solid Y<sub>2</sub>O<sub>3</sub> system

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## Abstract

The reactivity between liquid uranium and polycrystalline yttria substrates of various grain-sizes is studied at 1673 K under high vacuum–low  $p_{O_2}$  conditions ( $p_{O_2} \approx 10^{-7}$  Pa). At short contact times, uranium oxidation occurs at the metal/oxide interface from oxygen transferred from the yttria substrate which is transformed to an under-stoichiometric state. At long contact times, deoxidation occurring at the uranium free surface predominates and leads to complete elimination of oxidized uranium by a dissolution–evaporation mechanism. © 1998 Elsevier Science B.V.

## 1. Introduction

In the search for liquid uranium-resistant refractory ceramics, yttrium oxide is interesting because of its greater thermodynamic stability in comparison with UO<sub>2</sub>. For example, at 1673 K the standard Gibbs energy of formation for Y<sub>2</sub>O<sub>3</sub> is  $-476$  kJ/at g O compared to  $-398$  kJ/at g O for UO<sub>2</sub> [1]. Moreover, interactions between molten uranium and yttrium are very weak as evidenced by the very low solubility of Y in molten U (close to 0.5 at.% at  $T = 1700$  K [2]).

Despite these thermodynamic considerations, the formation of reaction products in U/Y<sub>2</sub>O<sub>3</sub> system has been previously reported [3,4].

In the present work, the reactivity of liquid U/Y<sub>2</sub>O<sub>3</sub> couple is studied at 1673 K as a function of time up to 200 h. The aim of this study is to identify the type of reactions occurring in this system as well as the mechanisms responsible. The effect of these reactions on wetting of yttria by uranium is discussed elsewhere [5,6].

## 2. Experimental method

The experiments are carried out in a metallic furnace heated by molybdenum resistance under a dynamic vac-








uum better than  $10^{-3}$  Pa obtained by an oil diffusion pump. In order to decrease the oxygen partial pressure  $p_{O_2}$  in the furnace, the specimens are placed in a tantalum isothermal chamber in which the value of oxygen partial pressure,  $p_{O_2}$ , was evaluated at  $p_{O_2} \approx 10^{-7}$  Pa [6].

Uranium used in this study contains 35 ppm of oxygen and 100 ppm of carbon. Aluminium, chromium, iron and nickel are the most important metallic impurities, with a total content of 30 ppm. Parallelepipedic uranium samples of 5 g are machined before testing.

The Y<sub>2</sub>O<sub>3</sub> samples have a thickness of 2 mm and a diameter of 20 mm. The substrate is polished to a roughness of about 1 nm. Yttria substrates of 1  $\mu$ m grain-size were produced by hot isostatic pressing at 1673 K under 150 MPa for 1 h, using a 99.999% pure powder. A limited number of experiments were performed with substrates of 6  $\mu$ m grain-size produced by sintering at 2073 K under vacuum for 3 h. Yttria can be under-stoichiometric, Y<sub>2</sub>O<sub>3-x</sub>, due to oxygen vacancies. The maximum value of  $x$  at 1673 K, corresponding to Y/Y<sub>2</sub>O<sub>3</sub> equilibrium, is about 0.08 [7,8]. The stoichiometry of yttria is roughly indicated by its colour, changing from white to black as the oxygen concentration decreases. HIP substrates are white while sintered yttria is black. Before experiments, the latter substrates are transformed to white by oxidation in air at 1773 K for 2 h. Experiments consist in heating the samples to the experimental temperature (1673 K) at a rate

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Table 1  
Results of reaction product thickness for polycrystalline yttria ( $d_g = 1 \mu\text{m}$  and  $d_g = 6 \mu\text{m}$ ) after contact with liquid U at 1673

Time (hours)	Grain-size of yttria (microns)	Substoichiometric zone in the substrate	Reaction product thickness (microns)	
			UO <sub>2</sub>	(U,Y)O <sub>x</sub>
1	1		2	traces
	6		0.5	traces
3	1		3.5	traces
12.5	1		6.5	traces
50	1		4.4	2.5
	6		7	traces
200	1		-	7

The black color of the substrate means under-stoichiometry.

of 5 K/min, maintaining the sample at this temperature for a certain time (from 1 to 200 h) and then cooling at room temperature at a rate of 50 K/min. After cooling, the reaction product morphology and chemistry are characterized by optical microscopy, microprobe, SEM and X-ray diffraction.

### 3. Results

The results obtained at 1673 K are given in Table 1. The change in stoichiometry of the substrate indicated by its colour, white for stoichiometric to black for under-stoichiometric, are also given schematically. The thickness of reaction products is measured at the interface far from the triple line (Fig. 1). Two reaction products were identified by X-ray diffraction: the U dioxide UO<sub>2</sub> and a UO<sub>2</sub>-Y<sub>2</sub>O<sub>3</sub> solid solution [9] denoted (U,Y)O<sub>x</sub>. Its compo-

sition was found by microprobe analysis to be close to U<sub>0.6</sub>Y<sub>0.4</sub>O<sub>2.1</sub>. Like UO<sub>2</sub>, the structure of (U,Y)O<sub>x</sub> is fcc with  $a = 0.536 \text{ nm}$  against a value  $a = 0.5496 \text{ nm}$  for UO<sub>2</sub> [6].

From the results of Table 1, it appears that a qualitative change is produced between 12.5 and 50 h. For  $t \leq 12.5 \text{ h}$  the reaction product at the interface is UO<sub>2</sub>. Its thickness, measured by S.E.M., increases rapidly with time. X-ray diffraction shows the presence of (U,Y)O<sub>x</sub> as well but only in traces. Between  $t = 12.5 \text{ h}$  and  $t = 50 \text{ h}$ , the total thickness of reaction product zone did not seem to vary. However, a significant part of the UO<sub>2</sub> was transformed into (U,Y)O<sub>x</sub>. At  $t = 50 \text{ h}$ , from chemical analysis of the solidified drop, the mole fraction of oxygen in uranium was found to be  $X_{\text{O}} = 1.2 \times 10^{-3}$ . At  $t = 200 \text{ h}$ , all the UO<sub>2</sub> layer was transformed into (U,Y)O<sub>x</sub>. In this case, from chemical analysis of the solidified drop, the mole fraction of yttrium dissolved in uranium was found to be  $X_{\text{Y}} = 2.4 \times 10^{-4}$ . The substrate, all white at the beginning of the experiment, becomes black close to the metal/yttria interface. For  $t \leq 12.5 \text{ h}$ , only part of the substrate is black.

However, the black area increases with time and, at  $t = 50 \text{ h}$  and  $t = 200 \text{ h}$ , all the yttria substrate is uniformly black. Attempts to measure the stoichiometric parameter  $x$  of Y<sub>2</sub>O<sub>3-x</sub> of black yttria by microprobe analysis were unsuccessful due to the lack of precision of oxygen concentration measurement.

During cooling, the differences in the linear expansion coefficients between the metallic drop and the ceramic substrate lead to systematic fracture partly at the interface and partly in the substrate (mixed fracture) (Fig. 1).

When the grain-size of yttria increases, the uranium oxidation rate at the interface decreases strongly for the short duration experiment ( $t = 1 \text{ h}$ ). However, no difference in the thickness of reaction products exists between the two grain-size substrates at  $t = 50 \text{ h}$ .

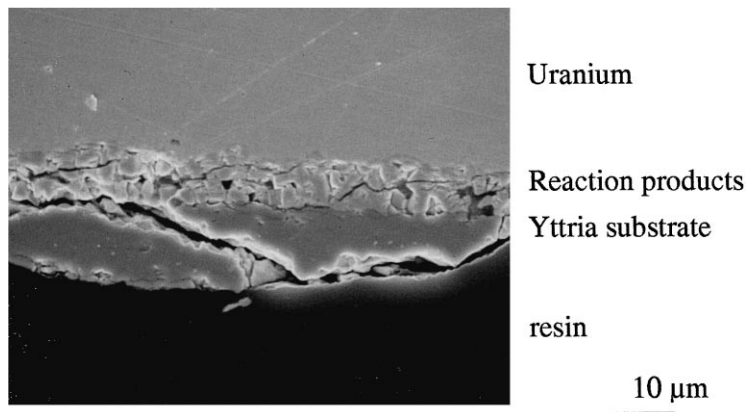


Fig. 1. Cross-section of the drop/substrate interface (SEM) ( $t = 200 \text{ h}$ ,  $T = 1673 \text{ K}$ ,  $d_g = 1 \mu\text{m}$ ). During cooling, thermomechanical stress led to cracks partly at the interface and partly in the substrate.

Finally, when the temperature increases by 100 K for yttria with  $d_g = 1 \mu\text{m}$ , no reaction products were visible at the interface after 50 h. However, the roughness of this interface is high (several microns) compared with the initial roughness of only a few nanometers. During cooling, the drop detached from the substrate by a cohesive fracture (Fig. 2). From chemical analysis, the mole fraction of oxygen dissolved in uranium was found to be  $X_{\text{O}} \approx 10^{-4}$  which is lower by a factor 10 than the value measured when  $\text{UO}_2$  was present at the interface

#### 4. Discussion

During isothermal holding at 1673 K, two opposite reactions occur in the  $\text{U}/\text{Y}_2\text{O}_3/\text{vapour}$  system. The first is uranium oxidation, the second uranium deoxidation.

##### 4.1. U oxidation at the $\text{U}/\text{Y}_2\text{O}_3$ interface: oxygen flow

Oxidation of uranium at the interface may be due to oxygen provided by yttria, leading to an increase in  $x$  in  $\text{Y}_2\text{O}_{3-x}$ , as well as to oxygen provided by the furnace atmosphere. The maximum thickness of  $\text{UO}_2$  formed by oxygen of the furnace may be evaluated by calculating the oxygen flow,  $\Phi_{\text{O}}$ , arriving on the free surface of the substrate, according to the molecular flow equation [10]:

$$\Phi_{\text{O}} = (\sum \alpha_i a_i p_i) / (2 M_i R T)^{1/2}, \quad (1)$$

in which  $p_i$  is the equilibrium partial pressure of the vaporising molecule  $i$ ,  $\alpha_i$  is the vaporisation coefficient ( $\alpha_i \leq 1$ ),  $a_i$ , the number of oxygen atoms in the molecule,  $M_i$ , the molar mass of the molecule, and  $R$  the ideal gas constant.

In our case, the expression for the oxygen flow is

$$\Phi_{\text{O}}^f = 2 \alpha_{\text{O}_2} p_{\text{O}_2}^f / (2 M_{\text{O}_2} R T)^{1/2}, \quad (2)$$

where  $p_{\text{O}_2}^f$  is the oxygen partial pressure in the furnace.

Taking  $\alpha_{\text{O}_2} = 1$ , the maximum value of impinging oxygen flow is calculated:

$$\Phi_{\text{O}}^f \text{ (in mol m}^{-2} \text{ s}^{-1}) = 3.8 \times 10^{-2} p_{\text{O}_2}^f \text{ (in Pa)}.$$

Then, the maximum thickness of  $\text{UO}_2$  layer which can be produced from furnace oxygen is written:

$$e_{\text{UO}_2}^{\text{max}} = (M_{\text{UO}_2} \Phi_{\text{O}}^f \Omega_s / 2 \Omega_i \rho_{\text{UO}_2}) t = 3 \times 10^3 p_{\text{O}_2}^f t, \quad (3)$$

where  $\Omega_s$  is the area of substrate surface collecting oxygen (equal to the area of a 20 mm diameter substrate),  $\Omega_i$  is the area of the drop/substrate interface (10 mm in diameter) and  $\rho_{\text{UO}_2}$  is the mass volume of  $\text{UO}_2$  ( $\approx 11 \times 10^3 \text{ kg m}^{-3}$ ). The thickness  $e_{\text{UO}_2}$  is in microns when  $p_{\text{O}_2}^f$  is in Pa and  $t$  in hours. Taking  $p_{\text{O}_2}^f = 10^{-7} \text{ Pa}$  and  $t = 1 \text{ h}$ , we find  $e_{\text{UO}_2}^{\text{max}} = 3 \times 10^{-4} \mu\text{m}$  which is negligible compared with the experimental value observed at  $t = 1 \text{ h}$  (Table 1). Clearly, in such low  $p_{\text{O}_2}$  atmospheres, oxidation of uranium at the interface is mainly due to the oxygen provided by the substrate. This conclusion is valid for all combinations of parameters  $t$  and  $p_{\text{O}_2}^f$  for which  $e_{\text{UO}_2}^{\text{max}}$  is less than a ‘measurable’ value of thickness, say  $10^{-1} \mu\text{m}$ . Conversely, for long durations and/or high  $p_{\text{O}_2}^f$  values, it may be expected that the furnace oxygen would contribute to interfacial oxidation of uranium. Indeed, as is described elsewhere, experiments performed with  $t = 50 \text{ h}$  and  $p_{\text{O}_2}^f = 10^{-4} \text{ Pa}$  led to  $e_{\text{UO}_2} \approx 20 \mu\text{m}$ , significantly more than the  $7 \mu\text{m}$  obtained for the same time at  $p_{\text{O}_2} = 10^{-7} \text{ Pa}$  (Table 1) [6].

In low  $p_{\text{O}_2}$  atmosphere, stoichiometric yttria provides oxygen to uranium, becoming itself sub-stoichiometric. This is consistent with the observation that yttria becomes black near the interface and that the black area progresses, until all the substrate becomes black. At this point, the oxygen of the substrate available for uranium oxidation is completely consumed and consequently, the growth of  $\text{UO}_2$  layer is stopped. It is reasonable to assume that the value of  $x$  in  $\text{Y}_2\text{O}_{3-x}$  corresponds to the  $p_{\text{O}_2}$  value fixed

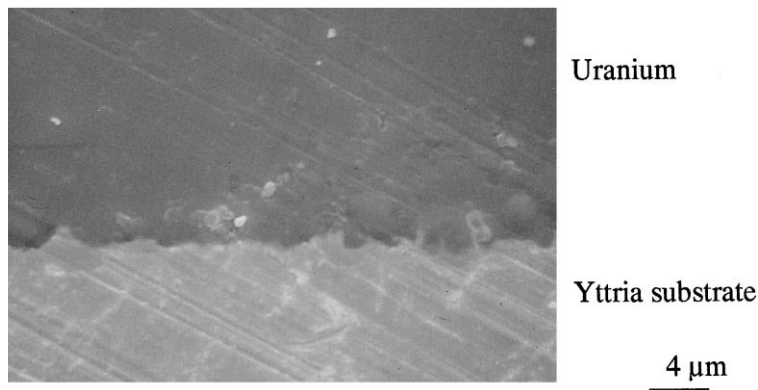


Fig. 2. Cross-section of the drop/substrate interface (SEM) ( $t = 50 \text{ h}$ ,  $T = 1773 \text{ K}$ ,  $d_g = 1 \mu\text{m}$ ). Interface is rough, but no reaction products are seen.

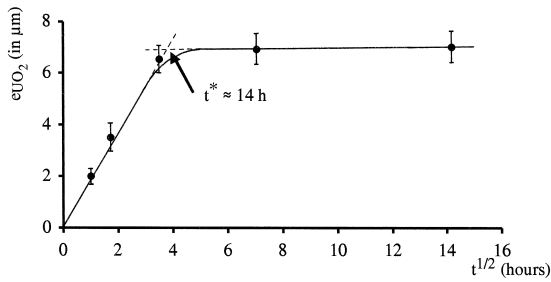


Fig. 3. Total thickness of reaction products plotted versus square root of time for  $d_g = 1 \mu\text{m}$  and  $T = 1673 \text{ K}$ .

at the interface by  $\text{U}/\text{UO}_{2-z}$  equilibrium, i.e.,  $p_{\text{O}_2} \approx 1.4 \times 10^{-20} \text{ Pa}$  at  $1673 \text{ K}$  [1]. This assumption is confirmed by the fact that the measured value of the mole fraction of oxygen dissolved in uranium was  $X_{\text{O}} = 1.2 \times 10^{-3}$  in good agreement with the value  $X_{\text{O}} = 1.3 \times 10^{-3}$  given for the  $\text{U}/\text{UO}_{2-z}$  system at the same temperature in Ref. [11]. Moreover, Gardie and Bordier [4] measured the  $p_{\text{O}_2}$  value in a liquid uranium/ $\text{Y}_2\text{O}_3$ /vapour system by mass spectroscopy and found values which are very close to those of  $\text{U}/\text{UO}_{2-z}$  equilibrium.

Once all the  $\text{UO}_2$  layer has been transformed to solid solution  $(\text{U},\text{Y})\text{O}_x$ , the partial pressure of oxygen at the interface is equal to the value corresponding to the three-phase equilibrium between molten U, solid solution  $(\text{U},\text{Y})\text{O}_x$  and  $\text{Y}_2\text{O}_3$  saturated in  $\text{UO}_2$ . This value, which is evaluated in Appendix A, is  $p_{\text{O}_2} \approx 10^{-23} \text{ Pa}$ .

#### 4.2. U oxidation at the $\text{U}/\text{Y}_2\text{O}_3$ interface: the rate limiting process

When the total thickness of interfacial reaction products is plotted as a function of square root of time, a quasi linear variation is obtained for  $0 \leq t \leq t^* = 14 \text{ h}$ , followed by a plateau (Fig. 3). The linear part of the curve indicates that growth of  $\text{UO}_2$  is controlled by diffusion.

Two diffusion mechanisms are possible, either diffusion through the growing  $\text{UO}_2$  layer or diffusion of oxygen from stoichiometric  $\text{Y}_2\text{O}_3$  (white areas) to the interface through an increasingly thick layer of under-stoichiometric yttria (black area). Two observations argue for the second hypothesis. First, the oxidation rate is higher near the triple line where the oxygen diffusion field in the substrate is much larger than at the interface far from the triple line. Secondly, for times  $t < t^*$ , the oxidation rate depends significantly on grain-size of the substrate. Indeed at  $t = 1 \text{ h}$ , when the grain-size is increased by a factor 6,  $e_{\text{UO}_2}$  decreases by a factor 4 (Table 1). Such results suggest not only that  $\text{UO}_2$  growth is controlled by diffusion of oxygen in the  $\text{Y}_2\text{O}_3$  substrate, but also that this diffusion occurs preferentially at the yttria grain boundaries. Diffusion in

the polycrystalline yttria can be described using an effective diffusion coefficient,  $D_{\text{eff}}$ , given by

$$D_{\text{eff}} = (1 - F)D_{\text{L}} + FD_{\text{GB}}$$

with  $F$  the volumic fraction of grain boundaries,  $F = 2\delta/d_g$ ;  $\delta$  the grain-boundary width (taken as  $1 \text{ nm}$  [12,13];  $D_{\text{L}}$  and  $D_{\text{GB}}$  the lattice and grain-boundary diffusion coefficients respectively.

According to the above equation the contribution of grain boundaries to total diffusion depends on the values of ratio  $D_{\text{GB}}/D_{\text{L}}$  and  $F = 2\delta/d_g$ . Although  $F$  is a small number, ( $F$  is  $3 \times 10^{-4}$  for  $d_g = 6 \mu\text{m}$  and  $2 \times 10^{-3}$  for  $d_g = 1 \mu\text{m}$ ), the value of  $D_{\text{GB}}/D_{\text{L}}$  is often so high ( $10^5$ , [13]) that the lattice contribution to diffusion may be small and even negligible. In the latter case, the  $e_{\text{UO}_2}$  thickness would vary according to  $d_g^{1/2}$ . Such a dependence predicts that when the grain size of the substrate increases from  $d_g = 1 \mu\text{m}$  to  $d_g = 6 \mu\text{m}$ ,  $e_{\text{UO}_2}$  would decrease from  $2 \mu\text{m}$  to  $0.8 \mu\text{m}$  which agrees well with the experimental value of  $0.5 \mu\text{m}$ .

#### 4.3. U deoxidation

At  $t > t^* \approx 14 \text{ h}$ , the total thickness does not change but  $\text{UO}_2$  is gradually replaced by the solid solution  $(\text{U},\text{Y})\text{O}_x$ . Actually, as the molar volume of  $(\text{U},\text{Y})\text{O}_x$  is very close to that of  $\text{UO}_2$  (the ratio of unit cell volumes being 0.93), the formation of  $(\text{U},\text{Y})\text{O}_x$ , with formula  $\text{U}_{0.6}\text{Y}_{0.4}\text{O}_{2.1}$ , corresponds to a net decrease in the number of moles,  $n_{\text{U}}^{\text{ox}}$ , of oxidized uranium at the interface. When this number is calculated and plotted as a function of time (Fig. 4), it is seen that after an initial increase,  $n_{\text{U}}^{\text{ox}}$  passes through a maximum and then decreases towards 0. By extrapolation of this curve, it is found that the interface layer would completely disappear after about 500 h. Such a result was obtained after only 50 h by increasing temperature from  $1673$  to  $1773 \text{ K}$  (Fig. 2).

The general condition for uranium deoxidation is

$$\varnothing_{\text{O}}^{\text{e}} > \varnothing_{\text{O}}^{\text{d}} + \varnothing_{\text{O}}^{\text{f}},$$

where  $\varnothing_{\text{O}}^{\text{e}}$  is the oxygen evaporation flow,  $\varnothing_{\text{O}}^{\text{d}}$  is the flow of oxygen arriving at the interface provided by the sub-

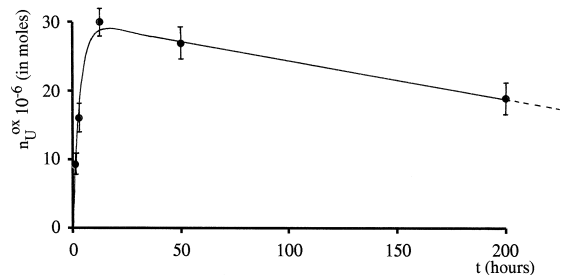


Fig. 4. Number of moles of oxidized uranium at the interface versus time. This number passes through a maximum for  $t \approx t^*$  and then decreases towards zero.

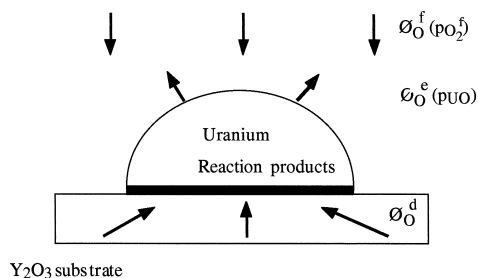


Fig. 5. Definition of the different oxygen flows in the liquid uranium/interfacial reaction products/yttria system.

strate, and  $\varnothing_O^f$  is the oxygen flow from the furnace atmosphere impinging on the drop surface (Fig. 5).

For  $t < t^*$ , the term  $\varnothing_O^d$  predominates, then  $\varnothing_O^d > \varnothing_O^e$  and oxidation occurs. For  $t > t^*$ , no more oxygen is available in the substrate for U oxidation, then  $\varnothing_O^d \approx 0$  and the condition for deoxidation of the drops becomes  $\varnothing_O^e > \varnothing_O^f \cdot \varnothing_O^f$  is roughly proportional to  $p_{O_2}$  in the furnace, equal to  $10^{-7}$  Pa. For evaluating  $\varnothing_O^e$ , it is noted that as long as a U-oxide layer is present at the U/Y<sub>2</sub>O<sub>3</sub> interface, deoxidation can occur by dissolution of this layer into the molten U, diffusion of dissolved oxygen from the interface to the drop surface and evaporation of oxygen from the free surface. As it was found by a mass spectroscopy investigation the oxygen containing molecule in the U<sub>(l)</sub>/Y<sub>2</sub>O<sub>3(s)</sub> system with the highest partial pressure at 1673 K is the U-monoxide [4,14]. Thus, the overall deoxidation reaction can be written as



Consequently, the evaporation flow of oxygen  $\varnothing_O^e$  is proportional to  $p_{UO}$ . The value of  $p_{UO}$ , fixed by the monovariant equilibrium reaction (5), is  $1.5 \times 10^{-4}$  Pa. This is much higher than the value of  $p_{O_2}^f = 10^{-7}$  Pa, meaning that deoxidation of uranium does occur. Note that a similar monovariant equilibrium involving Al<sub>2</sub>O<sub>3(s)</sub>, Al<sub>(l)</sub> and Al<sub>2</sub>O<sub>(g)</sub> phases was used in Ref. [10] to explain deoxidation of liquid aluminum drops under high vacuum. Similarly deoxidation of AuSi droplets was explained by means of a monovariant equilibrium involving SiO<sub>2(s)</sub>, silicon dissolved in molten Au and SiO<sub>(g)</sub> [15].

Table 2  
Comparison between calculated and experimental values of deoxidation times at two temperatures

Temperature (K)	$p_{UO}$ (Pa)	$t_{min}^e$ (calculated) (h)	$t^e$ (experimental) (h)
1673	$1.5 \times 10^{-4}$	80	(500)
1773	$10^{-3}$	12	< 50

The value of 500 h was obtained by extrapolation of  $n_U^{ox}$  versus time curve, Fig. 4.

By introducing the equilibrium value of  $p_{UO}$  in expression (1), the evaporation flow of oxygen can be calculated taking  $\alpha_{UO} = 1$ . Then, the minimum time,  $t^e$ , needed to dissolve and evaporate a 7  $\mu$ m thick layer of UO<sub>2</sub> is calculated (Table 2) (in this semi-quantitative calculation, no difference will be made between UO<sub>2</sub> and (U,Y)O<sub>x</sub>). At 1673 K, this time is 80 h. From the results of Table 2, it is seen that the calculated values of  $t_{min}^e$  predict rather well the net acceleration of U-deoxidation due to an increase in temperature.

## 5. Conclusion

In the molten U/Y<sub>2</sub>O<sub>3</sub> system under a high vacuum–low  $p_{O_2}$  atmosphere, two types of reaction occur:

Oxidation of uranium at the interface from oxygen provided by stoichiometric yttria which is transformed to under-stoichiometric yttria. This reaction predominates for short contact times as long as oxygen for U-oxidation is available in the yttria. The rate of reaction is controlled by diffusion of oxygen at yttria grain boundaries. For this reason, the oxidation reaction rate is sensitive to the grain size of the yttria substrate. The UO<sub>2</sub> layer, formed initially at the interface, is gradually transformed into a UO<sub>2</sub>–Y<sub>2</sub>O<sub>3</sub> solid solution.

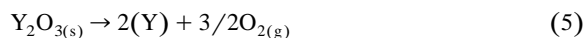
Deoxidation of uranium, occurring by a dissolution–evaporation mechanism. This process is effective for long contact times and leads to complete elimination of any reaction products from the U/Y<sub>2</sub>O<sub>3</sub> interface. During the above reactions and because of them the partial pressure of oxygen in the vicinity of the U/Y<sub>2</sub>O<sub>3</sub> interface decreases gradually from  $10^{-7}$  Pa to  $10^{-23}$  Pa. This has a considerable effect on the wetting and the adhesion energy of uranium on yttria, as discussed elsewhere [16].

## Appendix A

The value of  $p_{O_2}$  for the equilibrium of three phases, molten U–(U,Y)O<sub>x</sub>–Y<sub>2</sub>O<sub>3</sub> saturated in UO<sub>2</sub>, can be calculated from the experimental values of the mole fraction  $X_Y^*$  of Y dissolved in molten U in equilibrium with (U,Y)O<sub>x</sub> and Y<sub>2</sub>O<sub>3</sub>. At 1673 K, we measured  $X_Y^* = 2.4 \times 10^{-4}$ .

For high dilutions, the activity coefficient of Y in U is nearly constant (Henry's law), thus the activity  $a_Y^*$  is  $2.4 \times 10^{-4} / 4.3 \times 10^{-3} = 0.056$ , where  $4.3 \times 10^{-3}$  is the mole fraction of Y in molten U in equilibrium with pure solid yttrium [2].

For the reaction



(where the parentheses mean that yttrium is dissolved in U), the equilibrium constant is written

$$K = (a_Y)^2 p_{O_2}^{3/2} / a_{Y_2O_3}$$

$K$  is calculated from standard Gibbs free energy data of Ref. [1]. Then, taking  $a_{Y_2O_3} \approx 1$  and  $a_Y^* = 0.056$ , we find  $p_{O_2} = 9 \times 10^{-24}$  Pa.

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